PAZ107F

PAZ108F

Unit: mm

2: Collector

Unit: mm

3: Emitter MTGFR103-002 Package

MTGFR102-001 Package

PNZ107F (PN107F), **PNZ108F** (PN108F)

Silicon planar type

For optical control systems

■ Features

- Flat window design which is suited to optical systems
- Wide directivity characteristics for easy use
- Fast response: $t_r = 8 \mu s$ (typ.)
- Signal mixing capability using base pin (PNZ108F)
- TO-18 standard type package

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter		Symbol	Rating	Unit	
Collector-emitter voltage (Base open)		V_{CEO}	20	V	
Collector-base voltage	PNZ108F	V_{CBO}	30	V	
(Emitter open)					
Emitter-collector voltage (Base open)		V _{ECO}	3	V	
Emitter-base voltage	PNZ108F	V_{EBO}	5	V	
(Collector open)					
Collector current	$I_{\rm C}$	30	mA		
Collector power dissipation *		P_{C}	150	mW	
Operating ambient temperature		Topr	-25 to +85	°C	
Storage temperature		$T_{\rm stg}$	-30 to +100	°C	

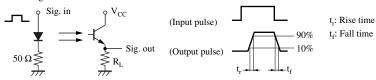
Note) *: The rate of electric power reduction is 1.5 mW/°C above $T_a = 25$ °C.

r dissipation * P_C 150 mW ent temperature T_{opr} -25 to +85 °C ature T_{stg} -30 to +100 °C

■ Electrical-Optical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

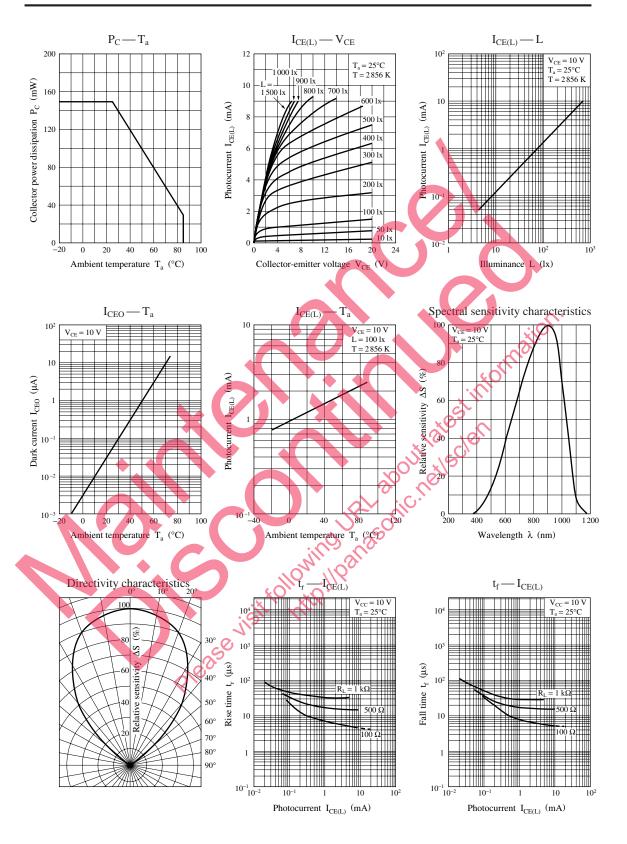
Parameter Symb		Conditions	Min	Тур	Max	Unit
Photocurrent *1	$I_{CE(L)}$	$V_{CE} = 10 \text{ V} \cdot L = 100 \text{ J} \times$	0.4		4.0	mA
Dark current	I _{CEO}	$V_{CE} = 10 \text{ V}$		0.05	2.0	μΑ
Peak emission wavelength	λ_{p}	V _{CE} = 10 V ○		900		nm
Half-power angle	θ	The angle from which photocurrent		40		٥
		becomes 50%				
Rise time *2	C.	$V_{CC} = 10 \text{ V}, I_{CE(L)} = 1 \text{ mA}, R_L = 100 \Omega$		8		μs
Fall time *2	t _f			9		μs
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{CE(L)} = 1 \text{ mA}, L = 1000 \text{ lx}$		0.3	0.6	V

- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
 - 2. Spectral sensitivity characteristics: Sensitivity for wave length over 400 nm maximum sensitivity ratio is 100%.
 - 3. This device is designed be dis regarded radiation.
 - 4. *1: Source: Tungsten (color temperature 2856 K)
 - *2: Switching time measurement circuit



Note) The part numbers in the parenthesis show conventional part number.

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